

Features and Applications

- Low ON-state resistance.
- High-speed switching.
- Surface mount type device making the following possible.
 - Reduction in the number of manufacturing processes for 2SJ456-applied equipment.
 - High density surface mount applications.
 - Small size of 2SJ456-applied equipment.

TENTATIVE

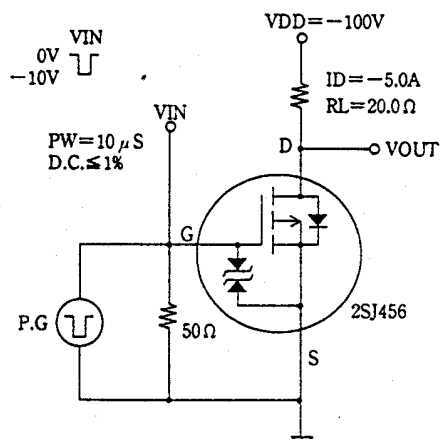
Absolute Maximum Ratings/Ta=25°C

			unit
Drain to Source Voltage	V _{DSS}	-250	V
Gate to Source Voltage	V _{GSS}	±30	V
Drain Current (DC)	I _D	-9	A
Drain Current (Pulse)	I _{DP} PW ≤ 10 μs, duty cycle ≤ 1%	-36	A
Allowable power Dissipation	PD TC=25°C	50	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

Electrical Characteristics/Ta=25°C

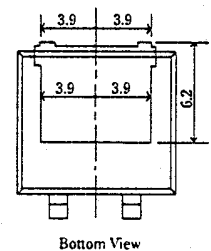
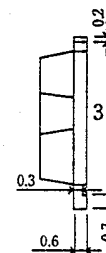
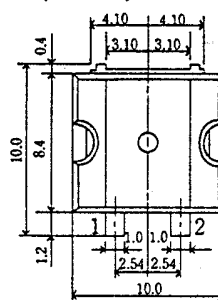
			min	typ	max	unit
D-S Breakdown Voltage	V(BR) _{DSS}	I _D = -1mA, V _{GS} = 0	-250			V
G-S Breakdown Voltage	V(BR) _{GSS}	I _G = ±100 μA, V _{DS} = 0	±30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -250V, V _{GS} = 0			-1.0	mA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±25V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-2.0		-3.0	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10V, I _D = -5A	4.8	8.0		S
Static Drain to Source ON-State Resistance	R _{DS(on)}	I _D = -5A, V _{GS} = -10V		0.4	0.55	Ω
Input Capacitance	C _{iss}	V _{DS} = -20V, f = 1MHz		1950		pF
Output Capacitance	C _{oss}	V _{DS} = -20V, f = 1MHz		505		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -20V, f = 1MHz		230		pF
Turn-ON Delay Time	t _{d(on)}	See Specified Test Circuit.		28		ns
Rise Time	t _r	"		125		ns
Turn-off Delay Time	t _{d(off)}	"		460		ns
Fall Time	t _f	"		160		ns
Diode Forward Voltage	V _{SD}	I _S = -9A, V _{GS} = 0	-1.0	-1.5		V
	t _{rr}	I _S = -9A, di/dt = 100A/μs		180		ns

Switching Time Test Circuit



Case Outline (unit:mm)

ZP(unit:mm)



- 1 : Gate
- 2 : Source
- 3 : Drain

Specifications and information herein are subject to change without notice.

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